

Substitute for form 1449A/PTO			<i>Complete if Known</i>	
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b> <i>(use as many sheets as necessary)</i>			Application Number	New Application <u>10/700719</u>
			Filing Date	November 5, 2003
			First Named Inventor	Tatsuya HONDA
			An Unit	<u>2825</u>
			Examiner Name	<u>PAUL DINH</u>
			Attorney Docket Number	740756-2664
Sheet	1	of	1	

U.S. PATENT DOCUMENTS					
Examiner Initials <sup>*</sup>	Cite No. <sup>1</sup>	U.S. Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
PD		US-5,442,174	08/15/1995	Kataoka et al.	
PD		US-5,502,305	03/26/1996	Kataoka	
PD		US-5,521,377	05/28/1996	Kataoka et al.	

FOREIGN PATENT DOCUMENTS						
Examiner Initials <sup>*</sup>	Cite No. <sup>1</sup>	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>
		Country Code <sup>3</sup> Number <sup>4</sup> Kind Code <sup>2</sup> (if known)				
PD		JP 07-66258	03/10/1995	Kataoka et al.		Abstract

OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials <sup>*</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>7</sup>
PD		Wen-Chin LEE et al., "Observation of Reduced Poly-Gate Depletion Effect for Poly-Si <sub>0.8</sub> Ge <sub>0.2</sub> -Gated NMOS Devices", Electrochemical and Solid-State Letter, 1(1), 1998, pp. 58-59.	
PD		C.J. KANG et al., "Charge trap dynamics in a SiO <sub>2</sub> layer on Si by scanning capacitance microscopy", Applied Physics Letters Vol. 74, No. 13, March 29, 1999, pp. 1815-1817.	

Examiner Signature	<u>Paul Dinh</u>	Date Considered	<u>4/4/06</u>
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\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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